

## UV-KUB 2 *4" version* *6" version*

UV LED exposure-masking system

*The UV-KUB 2 is a **very compact exposure and masking system** equipped with a **LED based optical head, collimated and homogenous.***

Controlled by touchscreen, the UV-KUB 2 ensures safety through an **entirely closed exposure chamber**, with both hard or soft contact modes available. Thanks to its hermetic configuration, this equipment **doesn't need to be installed in a clean room.**



### Technological breakthroughs

#### High quality collimation

**Divergence angle below 2°** offers the possibility to work in masking mode on thick layers without altering the rendering of edges of the patterns.

This **high-quality collimation** allows to reach resolution down to the micrometre scale **without needing a vacuum contact mode.**

#### LED technology

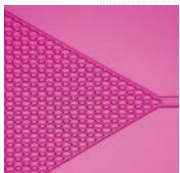
Perfectly **monochromatic** exposure light source.

A **cold UV source**, prevents undesirable thermal effects.

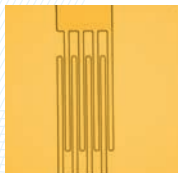
Possibility to operate in **continuous or pulse mode.**

**Long lifetime:** the uv-led light source is no longer considered as a consumable item.

### Related applications



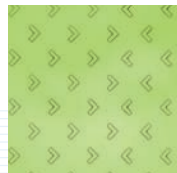
Microfluidics



Microelectronics



Photonics



Surface functionalization

# UV-KUB 2 *4" version* *6" version*

UV LED exposure-masking system

## Performances

Resolution	1µm
Divergence angle	< 2°
Number of programmable cycles	10
Exposure cycles (continuous/discontinuous)	From 1s to 1h
Processes	Hard (physical) or soft (proximity) contact processes

## UV-LED source

Wavelength	365nm +/- 5nm
Homogeneous exposure	+/- 5%
Lifetime of the LEDs	> 10 000 hours

## Working/Writing surfaces

Working surface	4" or 6" wafers
Substrate warm-up during exposure	< 1°C
Compatible photoresist	SU8, Shipley, AZ Resist, K-CL resist (developed by Kloe)

## Other features

- Size: 260(L) x 260(W) x 260(H)mm
- Weight: 8,2kg / 18lbs
- Colour touchscreen: 5,7" diagonal
- Power density: 35mW/cm<sup>2</sup> +/- 10%
- Power supply: 100V/240V - 50Hz/60Hz
- Consumption: 180W
- Distance control between the mask and the wafer: 10µm
- Full plate exposure: 6mm
- Substrate thickness + layers: maximum 2mm

